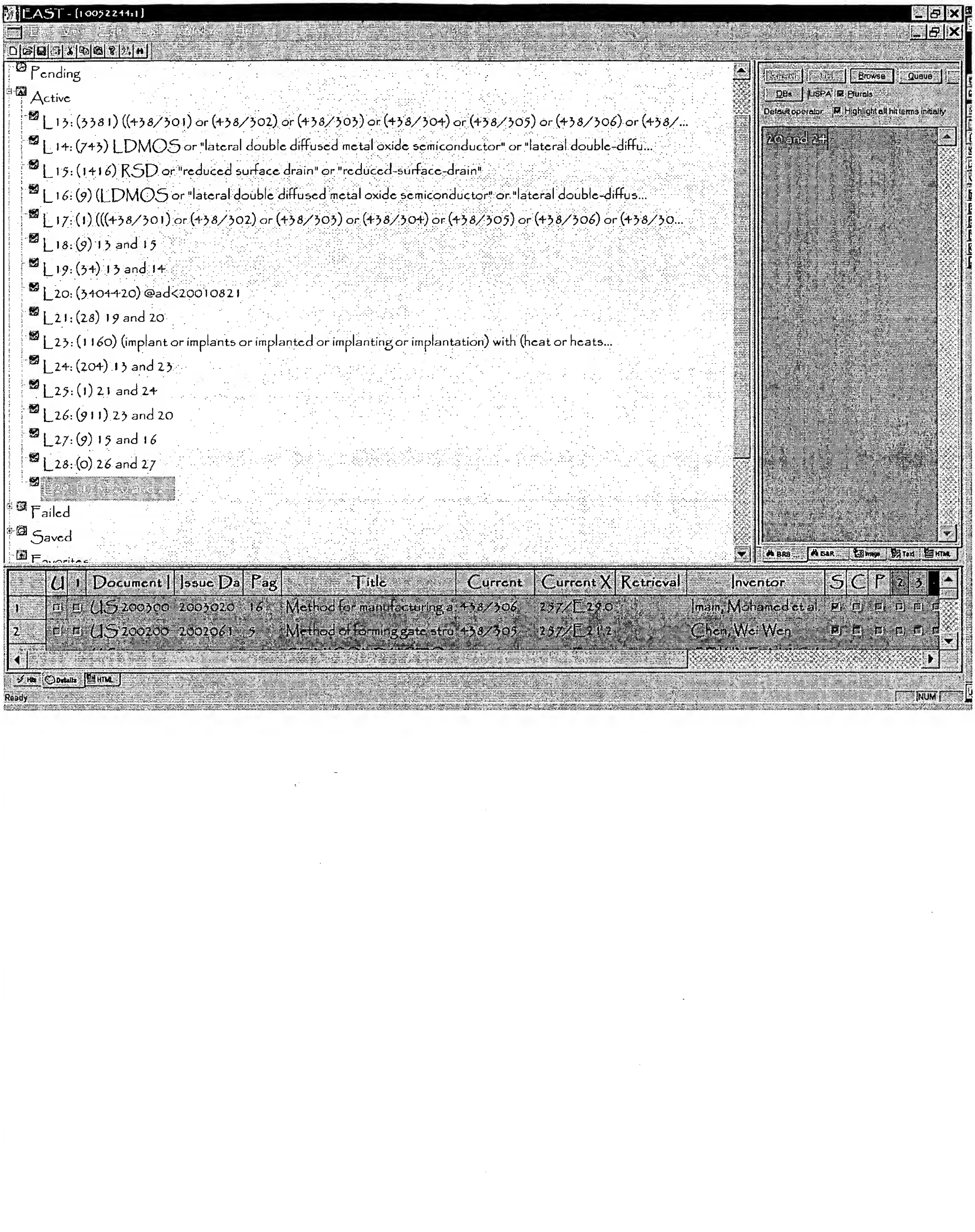
EAST - [10052244:1]
Pending
Active
L13: (3381) ((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/...
L14: (743) LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffu...
L15: (1416) RSD or "reduced surface drain" or "reduced-surface-drain"
L16: (9) (LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffus...
L17: (1) (((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/30...
L18: (9) 13 and 15
L19: (34) 13 and 14
L20: (3404420) @ad<20010821
L21: (28) 19 and 20
L23: (1160) (implant or implants or implanted or implanting or implantation) with (heat or heats...
L24: (204) 13 and 23
L25: (1) 21 and 24
L26: (911) 23 and 20
L27: (9) 15 and 16
L28: (0) 26 and 27
Failed
Saved
Search
Clear
Browse
Queue
DBs
USPA
Plurals
Default operator
Highlight all hit terms initially
20 and 24
BRS
SAR
Image
Text
HTML
U
Document I
Issue Da
Pag
Title
Current
Current X
Retrieval
Inventor
S
C
P
1
2
3
1 US 200300 2003020 16 Method for manufacturing a 438/306 257/E29.0 Imain, Mohamed et al.
2 US 200200 2002061 5 Method of forming gate stru 438/305 257/E21.2 Chen, Wei Wen
Hits
Details
HTML
Ready
NUM